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# EE C247B - ME C218

## Introduction to MEMS Design


### Fall 2019

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**Module 17: Noise & MDS**

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## Lecture Outline

- Reading: Senturia Chpt. 16
- Lecture Topics:
  - ↳ Minimum Detectable Signal
  - ↳ Noise
    - ↳ Circuit Noise Calculations
    - ↳ Noise Sources
    - ↳ Equivalent Input-Referred Noise
  - ↳ Gyro MDS
    - ↳ Equivalent Noise Circuit
    - ↳ Example ARW Determination

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## Determining Sensor Resolution

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## Minimum Detectable Signal (MDS)

- **Minimum Detectable Signal (MDS):** Input signal level when the signal-to-noise ratio (SNR) is equal to unity

Sensed Signal → [ Sensor Scale Factor + Sensor Noise ] → [ Circuit Gain + Circuit Output Noise ] → Output (Includes desired output plus noise)

- The sensor scale factor is governed by the sensor type
- The effect of noise is best determined via analysis of the equivalent circuit for the system

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# Noise

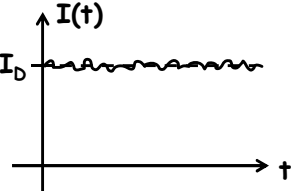
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# Noise

- **Noise:** Random fluctuation of a given parameter  $I(t)$
- In addition, a noise waveform has a zero average value

Avg. value (e.g. could be DC current)  $\rightarrow I_D$



- We can't handle noise at instantaneous times
- But we can handle some of the averaged effects of random fluctuations by giving noise a power spectral density representation
- Thus, represent noise by its mean-square value:  
Let  $i(t) = I(t) - I_D$   
Then  $\overline{i^2} = \overline{(I - I_D)^2} = \lim_{T \rightarrow \infty} \frac{1}{T} \int_0^T |I - I_D|^2 dt$

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### Noise Spectral Density

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- We can plot the spectral density of this mean-square value:

$\overline{i^2} =$  integrated mean-square noise spectral density over all frequencies (area under the curve)

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### Circuit Noise Calculations

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**Inputs**

$v_i(j\omega)$

$S_i(\omega)$

**Deterministic**

$H(j\omega)$

**Linear Time-Invariant System**

**Random**

**Outputs**

$v_o(j\omega)$

$S_o(\omega)$

*No  $j$  -> noise has random phase, so  $j$  is pointless!*

$v_o(t)$

$\frac{2\pi}{\omega_o}$

$v_o(j\omega)$

$S_o(t)$

$S_o(j\omega)$

**Mean square spectral density**

- Deterministic:**  $v_o(j\omega) = H(j\omega)v_i(j\omega)$
- Random:**  $S_o(\omega) = [H(j\omega)H^*(j\omega)]S_i(\omega) = |H(j\omega)|^2 S_i(\omega)$

$\sqrt{S_o(\omega)} = |H(j\omega)|\sqrt{S_i(\omega)}$      $\longrightarrow$     How is it we can do this?

**Root mean square amplitudes**

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### Handling Noise Deterministically

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- Can do this for noise in a tiny bandwidth (e.g., 1 Hz)

$\frac{v_{n1}^2}{\Delta f} = S_1(f) \rightarrow v_{n1} = \sqrt{S_1(f) \cdot B}$

Can approximate this by a sinusoidal voltage generator (especially for small B, say 1 Hz)

$\tau \sim \frac{1}{B}$

[This is actually the principle by which oscillators work → oscillators are just noise going through a tiny bandwidth filter]

Why? Neither the amplitude nor the phase of a signal can change appreciably within a time period 1/B.

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### Systematic Noise Calculation Procedure

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General Circuit With Several Noise Sources

- Assume noise sources are uncorrelated

- For  $i_{n1}^2$ , replace w/ a deterministic source of value

$$i_{n1} = \sqrt{\frac{i_{n1}^2}{\Delta f}} \cdot (1 \text{ Hz})$$

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## Systematic Noise Calculation Procedure

2. Calculate  $v_{on1}(\omega) = i_{n1}(\omega)H(j\omega)$  (treating it like a deterministic signal)
3. Determine  $\overline{v_{on1}^2} = \overline{i_{n1}^2} \cdot |H(j\omega)|^2$
4. Repeat for each noise source:  $\overline{i_{n1}^2}, \overline{v_{n2}^2}, \overline{v_{n3}^2}$
5. Add noise power (mean square values)
 
$$\overline{v_{onTOT}^2} = \overline{v_{on1}^2} + \overline{v_{on2}^2} + \overline{v_{on3}^2} + \overline{v_{on4}^2} + \dots$$

$$v_{onTOT} = \sqrt{\overline{v_{on1}^2} + \overline{v_{on2}^2} + \overline{v_{on3}^2} + \overline{v_{on4}^2} + \dots}$$


↖  
Total rms value

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## Noise Sources

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## Thermal Noise

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- **Thermal Noise in Electronics:** (Johnson noise, Nyquist noise)
  - ↳ Produced as a result of the thermally excited random motion of free e<sup>-</sup>'s in a conducting medium
  - ↳ Path of e<sup>-</sup>'s randomly oriented due to collisions
- **Thermal Noise in Mechanics:** (Brownian motion noise)
  - ↳ Thermal noise is associated with all dissipative processes that couple to the thermal domain
  - ↳ Any damping generates thermal noise, including gas damping, internal losses, etc.
- **Properties:**
  - ↳ Thermal noise is white (i.e., constant w/ frequency)
  - ↳ Proportional to temperature
  - ↳ Not associated with current
  - ↳ Present in any real physical resistor

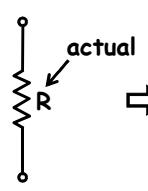
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## Circuit Representation of Thermal Noise

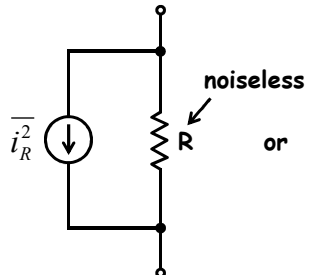
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- Thermal Noise can be shown to be represented by a series voltage generator  $\overline{v_R^2}$  or a shunt current generator  $\overline{i_R^2}$



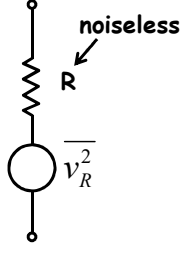
actual

⇒



noiseless

or



noiseless

$$\frac{\overline{i_R^2}}{\Delta f} = \frac{4kT}{R}$$

$$\frac{\overline{v_R^2}}{\Delta f} = 4kTR$$

Note: These are one-sided mean-square spectral densities! To make them 2-sided, must divide by 2.

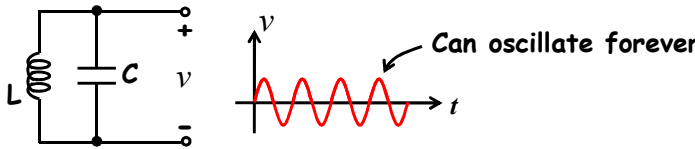
where  $4kT = 1.66 \times 10^{-20} V \cdot C$   
and where these are spectral densities.

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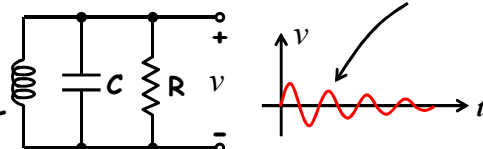
**Noise in Capacitors and Inductors?**

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- Resistors generate thermal noise
- Capacitors and inductors are noiseless → why?



- Now, add a resistor:



But this violates the laws of thermodynamics, which require that things be in constant motion at finite temperature

Need to add a forcing function, like a noise voltage  $\overline{v_R^2}$  to keep the motion going → and this noise source is associated with R

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**Why 4kTR?**

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- Why is  $\overline{v_R^2} = 4kTR\Delta f$  (a heuristic argument)
- The Equipartition Theorem of Statistical Thermodynamics says that there is a mean energy  $(1/2)kT$  associated w/ each degree of freedom in a given system
- An electronic circuit possesses two degrees of freedom:
  - ↪ Current,  $i$ , and voltage,  $v$
  - ↪ Thus, we can write:
 

$$\frac{1}{2}Li^2 = \frac{1}{2}k_B T \quad , \quad \overbrace{\frac{1}{2}Cv^2}^{\text{Energy}} = \frac{1}{2}k_B T$$
- Similar expressions can be written for mechanical systems
  - ↪ For example: for displacement,  $x$ 

$$\text{Spring constant} \quad \frac{1}{2}kx^2 = \frac{1}{2}k_B T$$

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**Why 4kTR? (cont)**

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- Why is  $\overline{v_R^2} = 4kTR\Delta f$ ? (a heuristic argument)
- Consider an RC circuit:

$E = \frac{1}{2}kT = \frac{1}{2}C\overline{v_C^2}$

$\therefore \overline{v_C^2} = \frac{kT}{C}$  ← integrated noise over all freqs.  
 (total mean square voltage integrated over all freqs.)

Question: What value of  $\frac{\overline{v_R^2}}{\Delta f}$  (assuming white noise) gives us this?

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**Why 4kTR? (cont)**

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Question: What value of  $\frac{\overline{v_R^2}}{\Delta f}$  (assuming white noise) gives us  $\overline{v_C^2} = \frac{kT}{C}$ ?

$\overline{v_C^2} = \int_0^\infty \left| \frac{1}{1+j\omega RC} \right|^2 \frac{\overline{v_R^2}}{\Delta f} d\omega$

[noise is white] →  $= \frac{1}{2\pi} \frac{\overline{v_R^2}}{\Delta f} \int_0^\infty \frac{\omega_b^2}{\omega_b^2 + \omega^2} d\omega$   
 [ $\omega_b = \frac{1}{RC}$ ]

$\left[ \int \frac{dx}{x^2+a^2} = \frac{1}{a} \tan^{-1}\left(\frac{x}{a}\right) \right]$

$= \frac{1}{2\pi} \frac{\overline{v_R^2}}{\Delta f} \frac{\omega_b^2}{\omega_b} \tan^{-1}\left(\frac{\omega}{\omega_b}\right) \Big|_0^\infty = \frac{1}{2\pi} \frac{\overline{v_R^2}}{\Delta f} \left( \frac{\pi}{2}\omega_b - 0 \right)$

$= \frac{1}{4} \omega_b \frac{\overline{v_R^2}}{\Delta f} = \frac{kT}{C} \rightarrow \frac{\overline{v_R^2}}{\Delta f} = 4kT \left( \frac{\omega_b}{C} \right) \Rightarrow \frac{\overline{v_R^2}}{\Delta f} = 4kTR \quad \checkmark$

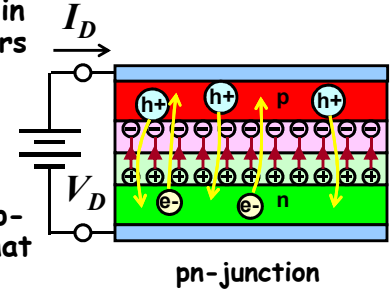
$\uparrow$   
R

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### Shot Noise

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- Associated with direct current flow in diodes and bipolar junction transistors
- Arises from the random nature by which e<sup>-</sup>s and h<sup>+</sup>s surmount the potential barrier at a pn junction
- The DC current in a forward-biased diode is composed of h<sup>+</sup>s from the p-region and e<sup>-</sup>s from the n-region that have sufficient energy to overcome the potential barrier at the junction  
 → noise process should be proportional to DC current
- Attributes:**
  - ↪ Related to DC current over a barrier
  - ↪ Independent of temperature
  - ↪ White (i.e., const. w/ frequency)
  - ↪ Noise power ~ I<sub>D</sub> & bandwidth



$$\frac{\overline{i_n^2}}{\Delta f} = 2qI_D$$

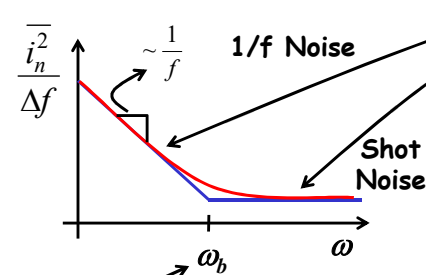
Charge on an e<sup>-</sup> (=1.6×10<sup>-19</sup>C)  
 DC Current

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### Flicker (1/f) Noise

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- In general, associated w/ random trapping & release of carriers from "slow" states
- Time constant associated with this process gives rise to a noise signal w/ energy concentrated at low frequencies
- Often, get a mean-square noise spectral density that looks like this:



$$\frac{\overline{i_n^2}}{\Delta f} = 2qI_D + K \left( \frac{I_D^a}{f^b} \right)$$

I<sub>D</sub> = DC current  
 K = const. for a particular device  
 a = 0.5 → 2  
 b ~ 1

1/f Noise Corner Frequency

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**Example: Typical Noise Numbers**  
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• Hookup the circuit below and make some measurements

Measure w/ AC voltmeter  
 Measure w/ spectrum analyzer  
 ← Get Gaussian amplitude distribution

Probability  
 Amplitude  
 68% within  $\pm \sigma$   
 99.7% within  $\pm 3\sigma$

$\frac{N_R^2}{\Delta f}$   
 $4kTR$   
 $\frac{1}{2\pi RC}$   
 $\text{area} \sim N_n^2$

$\frac{1k\Omega: 4nV/\sqrt{Hz}}{1pF: \sqrt{\frac{kT}{C}} = 64\mu V \text{ rms}}$  (for every 1k of R)

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**Example: Typical Noise Numbers**  
 UC Berkeley

• Hookup the circuit below and make some measurements

Measure w/ AC voltmeter  
 Measure w/ spectrum analyzer

AC Voltmeter  
 $\sqrt{N_o^2} = (100)(64\mu V \text{ rms}) = 6.4 \text{ mV rms}$

Spectrum Analyzer  
 $\frac{1}{(2\pi)(1k)(1p)} = 60 \text{ MHz}$   
 $400 \text{ nV}/\sqrt{Hz}$   
 $20 \text{ dB/dec}$   
 one-sided spectral density

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## Back to Determining Sensor Resolution

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## MEMS-Based Tuning Fork Gyroscope

(-) Sense Output Current

(+) Sense Output Current

From Sense

From Sense

From Sense

Instr. Amp

Demodulator

LPF

Rate Out

Drive Voltage Signal

Drive Electrode

Drive

Sense

$\Omega_z$

Sense Electrodes

Tuning Electrodes

Proof Mass

Proof Mass

Drive Electrode

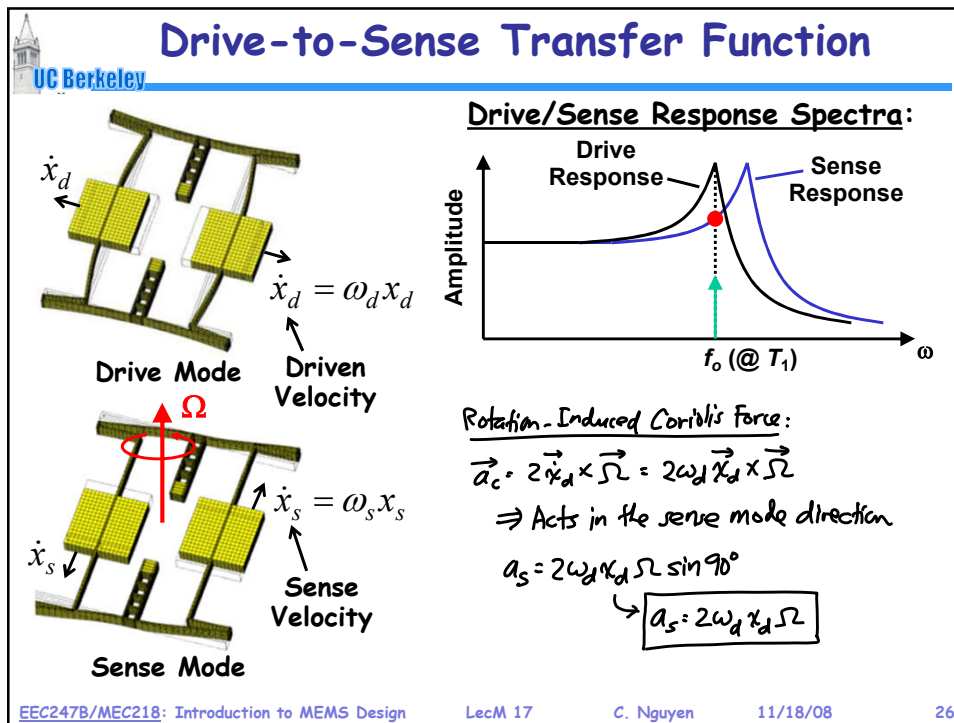
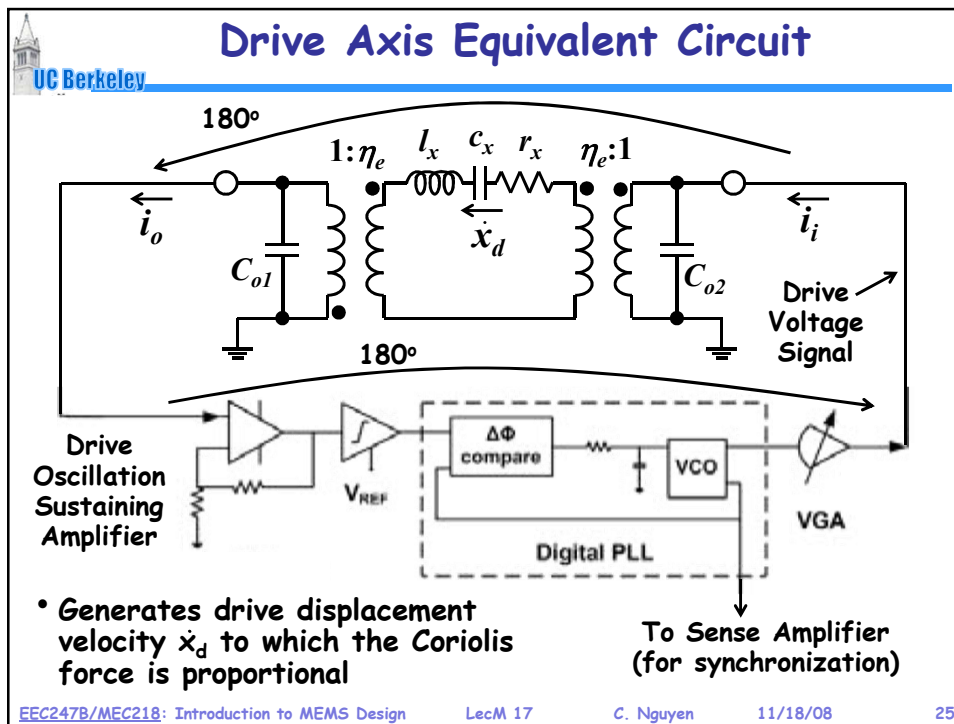
Drive

Drive Oscillation Sustaining Amplifier

Differential TransR Sense Amplifier

[Zaman, Ayazi, et al, MEMS'06]

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### Gyro Readout Equivalent Circuit (for a single tine)

$\vec{F}_c = m\vec{a}_c = m \cdot (2\vec{\dot{x}}_d \times \vec{\Omega})$

**Noise Sources**

**Gyro Sense Element Output Circuit**

**Signal Conditioning Circuit (Transresistance Amplifier)**

- Easiest to analyze if all noise sources are summed at a common node

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### Minimum Detectable Signal (MDS)

**Minimum Detectable Signal (MDS):** Input signal level when the signal-to-noise ratio (SNR) is equal to unity

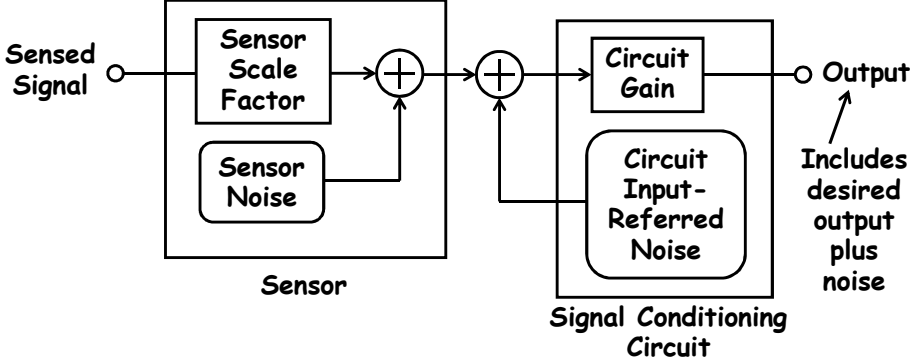
**Sensed Signal** → **Sensor** (Sensor Scale Factor, Sensor Noise) → **Signal Conditioning Circuit** (Circuit Gain, Circuit Output Noise) → **Output** (Includes desired output plus noise)

- The sensor scale factor is governed by the sensor type
- The effect of noise is best determined via analysis of the equivalent circuit for the system


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 **Move Noise Sources to a Common Point**

- Move noise sources so that all sum at the input to the amplifier circuit (i.e., at the output of the sense element)
- Then, can compare the output of the sensed signal directly to the noise at this node to get the MDS



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 **Equivalent Input-Referred Voltage and Current Noise Sources**

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## Equivalent Input $v$ , $i$ Noise Generators

- Take a noisy 2-port network and represent it by a noiseless network with input  $v$  and  $i$  noise generators that generate the same total output noise

- Remarks:**
  - Works for linear time-invariant networks
  - $v_{eq}$  and  $i_{eq}$  are generally correlated (since they are derived from the same sources)
  - In many practical circuits, one of  $v_{eq}$  and  $i_{eq}$  dominates, which removes the need to address correlation
  - If correlation is important  $\rightarrow$  easier to return to original network with internal noise sources

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## Calculation of $\overline{v_{eq}^2}$ and $\overline{i_{eq}^2}$

a) To get  $\overline{v_{eq}^2}$  for a two-port:

Case I

Case II

- Short input, find  $\overline{v_{0I}^2}$  (or  $\overline{i_{0I}^2}$ )
- For eq. network, short input, find  $\overline{v_{0II}^2}$  (or  $\overline{i_{0II}^2}$ )

$$\begin{array}{ccc} \parallel & & \parallel \\ f(\overline{v_{eq}^2}) & & f(\overline{v_{eq}^2}) \end{array}$$

- Set  $\overline{v_{0I}^2} = \overline{v_{0II}^2} \rightarrow$  solve for  $\overline{v_{eq}^2}$  (or  $\overline{i_{0I}^2} = \overline{i_{0II}^2}$ )

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## Calculation of $\overline{v_{eq}^2}$ and $\overline{i_{eq}^2}$ (cont)

b) To get  $\overline{i_{eq}^2}$  for a 2-port:

- 1) Open input, find  $\overline{v_{0I}^2}$  (or  $\overline{i_{0I}^2}$ )
- 2) Open input for eq. circuit, find  $\overline{v_{0II}^2}$  (or  $\overline{i_{0II}^2}$ )
- 3) Set  $\overline{v_{0I}^2} = \overline{v_{0II}^2} \left( \overline{i_{eq}^2} \right) \rightarrow$  solve for  $\overline{i_{eq}^2}$  (or  $\overline{i_{0I}^2} = \overline{i_{0II}^2} \left( \overline{i_{eq}^2} \right)$ )

- Once the equivalent input-referred noise generators are found, noise calculations become straightforward as long as the noise generators can be treated as uncorrelated

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## Cases Where Correlation Is Not Important

- There are two common cases where correlation can be ignored:
  1. Source resistance  $R_s$  is **small** compared to input resistance  $R_i \rightarrow$  i.e., voltage source input
  2. Source resistance  $R_s$  is **large** compared to input resistance  $R_i \rightarrow$  i.e., current source input

1)  $R_s = \text{small}$  (ideally = 0 for an ideal voltage source):

$\therefore$  For  $R_s = \text{small}$ ,  $\overline{i_{eq}^2}$  can be neglected  $\rightarrow$  only  $\overline{v_{eq}^2}$  is important!  
(Thus, we need not deal with correlation)

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**Cases Where Correlation Is Not Important**

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2)  $R_S = \text{large}$  (Ideally =  $\infty$  for an ideal current source)

Voltage  $\overline{v_{eq}^2}$  effectively "opened" out!

$$v_i = \frac{R_{in}}{\infty + R_{in}} v_{eq} = 0!$$

$\therefore$  For  $R_S = \text{large}$ ,  $\overline{v_{eq}^2}$  can be neglected!  
 $\rightarrow$  only  $\overline{i_{eq}^2}$  is important!  
 (... and again, we need not deal with correlation)

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**Example: TransR Amplifier Noise**

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**Case I**

**Input-referred current noise:**  
 Open inputs; equate output voltage noise.

Case I:  
 $N_{oI1} = i_{ia} R_f$   
 $N_{oI2} = i_f R_f$   
 $N_{oI3} = N_{ia}$   
 Move  $N_{ia}$  through  $R_{in}$  to  $N_{ia}$   $\rightarrow$  This is unity gain!

$\therefore N_{oI}^2 = i_{ia}^2 R_f^2 + i_f^2 R_f^2 + N_{ia}^2$

**Case II**

Case II:  $N_{oII}^2 = i_{eq}^2 R_f^2$

$\therefore \overline{i_{eq}^2} = \overline{i_{ia}^2} + \overline{i_f^2} + \frac{N_{ia}^2}{R_f^2}$

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**Example: TransR Amplifier Noise (cont)**

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**Input-referred voltage noise:**  
Short inputs; equate output voltage noise

**Case I:**  

$$\overline{N_{oI}^2} = \overline{N_{ia}^2} a^2$$
 (Both  $i_{ia}^2$  &  $i_f^2$  are shorted out.)

**Case II:**  

$$\overline{N_{oII}^2} = \overline{N_{eq}^2} a^2$$
  

$$\therefore \overline{N_{eq}^2} = \overline{N_{ia}^2}$$

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**Example: TransR Amplifier Noise (cont)**

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- To summarize, for a transresistance amplifier, the equivalent input-referred current and voltage noise generators are given by:

$$\overline{i_{eq}^2} = \overline{i_{ia}^2} + \overline{i_f^2} + \frac{\overline{v_{ia}^2}}{R_f^2}$$

$$\overline{v_{eq}^2} = \overline{v_{ia}^2}$$

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## Back to Gyro Noise & MDS

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### Example: Gyro MDS Calculation

$\vec{F}_c = m\vec{a}_c = m \cdot (2\vec{\dot{x}}_d \times \vec{\Omega})$

- The gyro sense presents a large effective source impedance
  - ↪ Currents are the important variable; voltages are "opened" out
  - ↪ Must compare  $i_o$  with the total current noise  $i_{eqTOT}$  going into the amplifier circuit

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**Example: Gyro MDS Calculation (cont)**

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$\vec{F}_c = m\vec{a}_c = m \cdot (2\vec{\dot{x}}_d \times \vec{\Omega})$

• First, find the rotation to  $i_o$  transfer function:

$$\dot{x}_s = \frac{\omega_s Q_s}{k_s} (H_s(j\omega_d)) F_s = \frac{\omega_s Q_s}{k_s} \cdot 2\omega_d \kappa_d \Omega m \cdot (H_s(j\omega_d))$$

$[F_s = F_c = 2\omega_d \kappa_d \Omega m]$

$$\dot{x}_s = 2 \frac{\omega_d}{\omega_s} Q_s \kappa_d (H_s(j\omega_d)) \cdot \Omega$$

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**Example: Gyro MDS Calculation (cont)**

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$$i_o = \eta_e \dot{x}_s = 2 \frac{\omega_d}{\omega_s} Q_s \kappa_d \eta_e (H_s(j\omega_d)) \cdot \Omega \Rightarrow i_o = A\Omega$$

$A \triangleq$  scale factor

Where  $A = 2 \frac{\omega_d}{\omega_s} Q_s \kappa_d \eta_e (H_s(j\omega_d))$

When  $\Omega = \Omega_{min} \triangleq$  MDS,  $i_o = i_{eqTOT}$  ← input-referred noise current entering the sense amplifier → in pA/√Hz

$$\therefore i_{eqTOT} = A\Omega_{min} \rightarrow \Omega_{min} = \frac{i_{eqTOT}}{A} \left( \frac{3600s}{hr} \right) \left( \frac{180^\circ}{\pi} \right) \left[ \left( \frac{\%}{hr} \right) / \sqrt{Hz} \right]$$

Angle Random Walk:  $ARW = \frac{1}{60} \Omega_{min} \left[ \frac{\circ}{\sqrt{hr}} \right]$

← Easier to determine directional error as a function of elapsed time.

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**Example: Gyro MDS Calculation (cont)**

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$\vec{F}_c = m\vec{a}_c = m \cdot (2\vec{\dot{x}}_d \times \vec{\Omega})$

• Now, find the  $i_{eqTOT}$  entering the amplifier input:

$$i_{eqTOT}^2 = i_s^2 + i_{eq}^2 \rightarrow i_{eqTOT}^2 = i_s^2 + i_f^2 + i_{ia}^2 + \frac{N_{ia}^2}{R_f^2}$$

$\frac{f_{rx}^2}{\Delta f} = 4kTR_x$

Brownian motion noise of the sense element  $\rightarrow$  determined entirely by the noise in  $r_x \rightarrow f_{rx}^2$   
 $\hookrightarrow$  easiest to convert to an all electrical equiv. ckt.

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**Example: Gyro MDS Calculation (cont)**

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where  $L_x = \frac{R_x}{\eta_e^2}$ ,  $C_x = \eta_e^2 C_x$ ,  $R_x = \frac{r_x}{\eta_e}$

$$\therefore i_s^2 = N_{R_x} \left( \frac{1}{R_x} \right) |H_s(j\omega_d)|^2 \rightarrow \frac{i_s^2}{\Delta f} = 4kTR_x \left( \frac{1}{R_x^2} \right) |H_s(j\omega_d)|^2$$

$$\Rightarrow \frac{i_s^2}{\Delta f} = \frac{4kT}{R_x} |H_s(j\omega_d)|^2$$

Thus:

$$\frac{i_{eqTOT}^2}{\Delta f} = \frac{4kT}{R_x} |H_s(j\omega_d)|^2 + \frac{4kT}{R_f} + \frac{i_{ia}^2}{\Delta f} + \frac{N_{ia}^2}{\Delta f} \left( \frac{1}{R_f^2} \right)$$

Learn to get there from EE240.  
 $\hookrightarrow$  or just get them from a data sheet ...

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### LF356 Op Amp Data Sheet

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#### LF155/LF156/LF256/LF257/LF355/LF356/LF357 JFET Input Operational Amplifiers

**General Description**

These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors (BI-FET™ Technology). These amplifiers feature low input bias and offset currents/low offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or common-mode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

**Common Features**

- Logarithmic amplifiers
- Photocell amplifiers
- Sample and Hold circuits
- Low input bias current: 30pA
- Low Input Offset Current: 3pA
- High input impedance:  $10^{12}\Omega$
- Low input noise current:  $0.01 \text{ pA}/\sqrt{\text{Hz}}$
- High common-mode rejection ratio: 100 dB
- Large dc voltage gain: 106 dB

**Features**

**Advantages**

- Replace expensive hybrid and module FET op amps
- Rugged JFETs allow blow-out free handling compared with MOSFET input devices
- Excellent for low noise applications using either high or low source impedance—very low 1/f corner
- Offset adjust does not degrade drift or common-mode rejection as in most monolithic amplifiers
- New output stage allows use of large capacitive loads (5,000 pF) without stability problems
- Internal compensation and large differential input voltage capability

**Applications**

- Precision high speed integrators
- Fast D/A and A/D converters
- High impedance buffers
- Wideband, low noise, low drift amplifiers

**Uncommon Features**

	LF155/ LF355	LF156/ LF256/ LF356	LF257/ LF357 ( $A_V=5$ )	Units
Extremely fast settling time to 0.01%	4	1.5	1.5	$\mu\text{s}$
Fast slew rate	5	12	50	V/ $\mu\text{s}$
Wide gain bandwidth	2.5	5	20	MHz
Low input noise voltage	20	12	12	nV/ $\sqrt{\text{Hz}}$

*Handwritten notes:*

- $\sqrt{\frac{i_{ia}^2}{\Delta f}} = 0.01 \text{ pA}/\sqrt{\text{Hz}}$
- $\sqrt{\frac{v_{ia}^2}{\Delta f}} = 12 \text{ nV}/\sqrt{\text{Hz}}$

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### Example ARW Calculation

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• **Example Design:**

↳ **Sensor Element:**

$$m = (100\mu\text{m})(100\mu\text{m})(20\mu\text{m})(2300\text{kg}/\text{m}^3) = 4.6 \times 10^{-10}\text{kg}$$

$$\omega_s = 2\pi(15\text{kHz})$$

$$\omega_d = 2\pi(10\text{kHz})$$

$$k_s = \omega_s^2 m = 4.09 \text{ N/m}$$

$$x_d = 20 \mu\text{m}$$

$$Q_s = 50,000$$

$$V_p = 5\text{V}$$

$$h = 20 \mu\text{m}$$

$$d = 1 \mu\text{m}$$

↳ **Sensing Circuitry:**

$$R_f = 100\text{k}\Omega$$

$$i_{ia} = 0.01 \text{ pA}/\sqrt{\text{Hz}}$$

$$v_{ia} = 12 \text{ nV}/\sqrt{\text{Hz}}$$

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**Example ARW Calculation (cont)**

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Get rotation rate to output current scale factor:

$$A = 2 \frac{\omega_d}{\omega_s} Q_s \eta_e \eta_c |\Theta_s(j\omega_d)| = 2 \left( \frac{10k}{15k} \right) (50k) (20\mu) (5) (2000\epsilon_0) (0.000024) = 2.83 \times 10^{-12} C$$

$$\Theta_s(j\omega_d) = \frac{(j\omega_d)(\omega_s/\omega_s)}{-\omega_d^2 + \frac{j\omega_d\omega_s}{Q_s} + \omega_s^2} = \frac{j(10k)(15k)/(50k)}{(15k)^2 - (10k)^2 + \frac{j(10k)(15k)}{50k}} = \frac{j(3k)}{1.25 \times 10^8 + j(3k)}$$

$$\Rightarrow |\Theta_s(j\omega_d)| = \frac{3k}{\sqrt{(1.25 \times 10^8)^2 + (3k)^2}} = 0.000024 \quad 8.854 \times 10^{-8} F/m$$

$$\frac{\partial C}{\partial x} = \frac{C_0}{d} = \frac{\epsilon_0 h \omega_p}{d} = \frac{\epsilon_0 (20\mu)(100\mu)}{(1\mu)^2} = 2000\epsilon_0 \rightarrow \eta_e = V_p \frac{\partial C}{\partial x} = 5(2000\epsilon_0) = 8.854 \times 10^{-12} F/m$$

Assume electrode covers the whole sidewall.

Then, get noise:

$$\frac{\overline{i_{eq}^2}}{\Delta f} = \frac{4kT}{R_x} |\Theta_s(j\omega_d)|^2 + \frac{4kT}{R_f} + \frac{\overline{i_{ia}^2}}{\Delta f} + \frac{\overline{N_{ie}^2}}{\Delta f} \left( \frac{1}{R_f} \right)$$

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**Example ARW Calculation (cont)**

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$$R_x = \frac{\omega_s m}{Q_s \eta_e^2} = \frac{2\pi(15k)(4.6 \times 10^{-10})}{(50k)(8.854 \times 10^{-8})^2} = 110.6 k\Omega$$

$$\frac{\overline{i_{eqTOT}^2}}{\Delta f} = \frac{(1.66 \times 10^{-29})}{(110.6k)} (0.000024)^2 + \frac{(1.66 \times 10^{-29})}{1M} + (0.01p)^2 + \frac{(12n)^2}{(1M)^2}$$

$8.64 \times 10^{-35} A^2/Hz$      $1.66 \times 10^{-26} A^2/Hz$      $1 \times 10^{-28} A^2/Hz$      $1.44 \times 10^{-28} A^2/Hz$   
 Sensor element noise insignificant    Noise from  $R_f$  dominates!

$$\therefore \frac{\overline{i_{eqTOT}^2}}{\Delta f} = 1.68 \times 10^{-26} A^2/Hz \rightarrow \overline{i_{eqTOT}} = \sqrt{\frac{\overline{i_{eqTOT}^2}}{\Delta f}} = 1.30 \times 10^{-13} A/\sqrt{Hz}$$

$$\therefore \Omega_{min} = \frac{\overline{i_{eqTOT}}}{A} \left( \frac{3600s}{hr} \right) \left( \frac{180^\circ}{\pi} \right) = \frac{1.30 \times 10^{-13}}{2.83 \times 10^{-12}} (3600) \left( \frac{180}{\pi} \right) = 9448 (\%/hr)/\sqrt{Hz}$$

And finally:

$$ARW = \frac{1}{60} \Omega_{min} = \frac{1}{60} (9448) = 157 \%/hr = ARW \Rightarrow \text{Almost turned around in 1 hour!}$$

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**What if  $\omega_d = \omega_s$ ?**

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If  $\omega_d = \omega_s = 15\text{kHz}$ , then  $|\Theta(j\omega_d)| = 1$  and

$$A = 2 \frac{\omega_d}{\omega_s} Q_s X_d \eta_e |\Theta(j\omega_d)| = 2 Q_s X_d \eta_e = 2(50\text{k})(20\mu)(5)(2000\text{e}_0) = 1.77 \times 10^{-7} \text{C}$$

$$\frac{i_{eqTOT}^2}{\Delta f} = \frac{(1.66 \times 10^{-29})^2}{(110.6\text{k})} + \frac{(1.66 \times 10^{-29})^2}{1\text{M}} + (0.01\text{p})^2 + \frac{(12\text{n})^2}{(1\text{M})^2}$$

$\swarrow 1.51 \times 10^{-25} \text{A}^2/\text{Hz}$    
 $\swarrow 1.66 \times 10^{-26} \text{A}^2/\text{Hz}$    
 $\swarrow 1 \times 10^{-28} \text{A}^2/\text{Hz}$    
 $\swarrow 1.44 \times 10^{-28} \text{A}^2/\text{Hz}$

Now, the sensor element dominates!

$$\therefore \frac{i_{eqTOT}^2}{\Delta f} = 1.67 \times 10^{-25} \text{A}^2/\text{Hz} \rightarrow i_{eqTOT} = \sqrt{\frac{i_{eqTOT}^2}{\Delta f}} = 4.08 \times 10^{-13} \text{A}/\sqrt{\text{Hz}}$$

$$\therefore \Sigma_{min} = \frac{i_{eqTOT}}{A} \left( \frac{3600\text{s}}{\text{hr}} \right) \left( \frac{180^\circ}{\pi} \right) = \frac{4.08 \times 10^{-13}}{1.77 \times 10^{-7}} (3600) \left( \frac{180}{\pi} \right) = 0.476 (\%/hr)/\sqrt{\text{Hz}}$$

And finally:

$$\text{ARW} = \frac{1}{60} \Sigma_{min} = \frac{1}{60} (0.476) = 0.0079 \%/hr = \text{ARW} \Rightarrow \text{Navigation grade!}$$

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